

#### SINGLE P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
  - $13m\Omega$  @  $V_{GS} = -10V$
  - 16mΩ @ V<sub>GS</sub> = -4.5V
  - 22mΩ @ V<sub>GS</sub> = -2.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMP2022LSSQ)

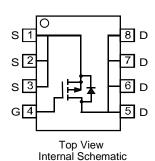
#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072g (Approximate)

SO-8



Top View



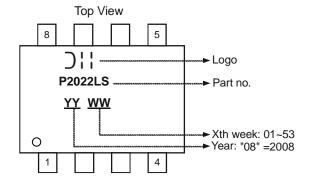
#### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP2022LSS-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**





### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Chara		Symbol	Value	Unit	
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V	
Drain Current (Note 5)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	-10 -8	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-90	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	50	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on 2 oz. Copper pads on FR-4 PCB.

6. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .

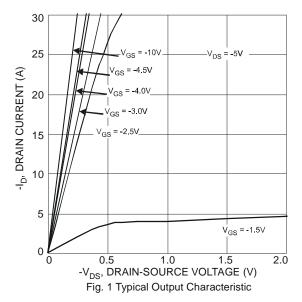
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
Characteristic Symbol Min Typ Max Unit Test Condition OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_		V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-1	μА	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						7 50	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.6	-0.77	-1.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
	55(,	_	8	13	mΩ	$V_{GS} = -10V, I_{D} = -10A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	11	16		$V_{GS} = -4.5V, I_{D} = -9A$	
	= = (= : : )	_	17	22		$V_{GS} = -2.5V, I_{D} = -8A$	
Forward Transconductance	g <sub>fs</sub>	_	28	_	S	$V_{DS} = -10V, I_{D} = -10A$	
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-0.5	-0.68	-1.2	V	$V_{GS} = 0V, I_{S} = -3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	2444	_	pF	10)/ )/	
Output Capacitance	Coss	_	594	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	556	_	pF	71 = 1.0WHZ	
Gate Resistance	R <sub>G</sub>	_	2.0	_	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	$Q_g$	_	28.1 56.9	_		$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $I_{D} = -10A$ $V_{DS} = -10V$ , $V_{GS} = -10V$ , $I_{D} = -10A$	
Gate-Source Charge	Q <sub>qs</sub>	_	3.4	_	nC	$V_{DS} = -10V$ , $V_{GS} = -10V$ , $I_{D} = -10A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	11.9	_		$V_{DS} = -10V$ , $V_{GS} = -10V$ , $I_{D} = -10A$	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.5	15	$V_{DD} = -15V$ , $I_{D} = -1A$ , $V_{GS} = -10$ $R_{GEN} = 6\Omega$		
Turn-On Rise Time	t <sub>R</sub>	_	9.9	20			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	108.0	216			
Turn-Off Fall Time	t <sub>F</sub>	_	76.5	153			

Notes: 7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





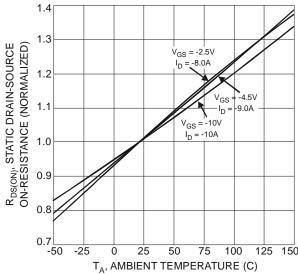
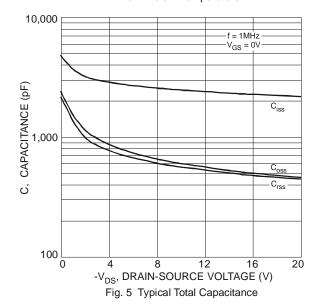


Fig. 3 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



30  $V_{DS} = -5V$ Pulsed 25 -I<sub>D</sub>, DRAIN CURRENT (A) 20 15 10 T<sub>A</sub> = 125°C 5 = -55°C 0 0.5 2.5  $-V_{GS}$ , GATE SOURCE VOLTAGE (V) Fig. 2 Typical Transfer Characteristics

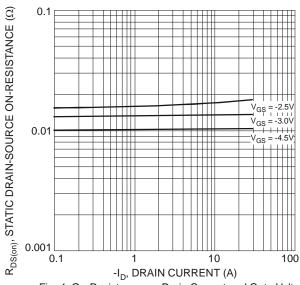


Fig. 4 On-Resistance vs. Drain Current and Gate Voltage

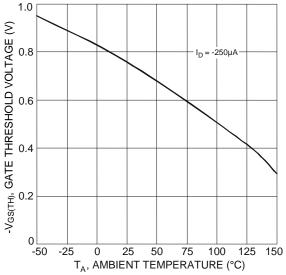


Fig. 6 Gate Threshold Variation vs. Ambient Temperature



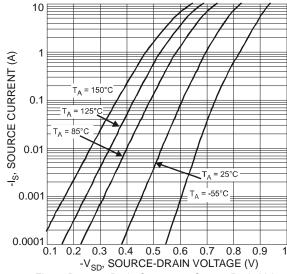
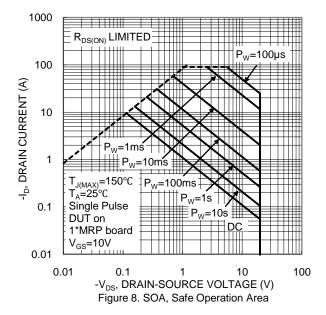


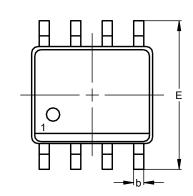
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

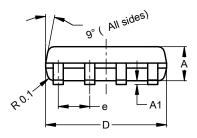


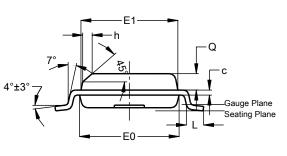


# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





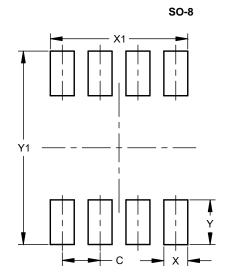


SO-8

SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	1		0.35		
L	0.62	0.82	0.72		
ø	0.60	0.70	0.65		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



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